

JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOP8 Plastic-Encapsulate MOSFETS

CJQ4407 P-Channel Power MOSFET

$V_{(BR)DSS}$	R _{DS(on)} MAX	I _D
201/	13mΩ@-10V	
-30 V	17mΩ@-6V	-12A

SOP8 8 7 6 5 1 2 3 4

DESCRIPTION

The CJQ4407 combines advanced trench MOSFET technology with a low resistance package to provide extremely low RDS(ON). This device is ideal for load switch and battery protection applications

APPLICATIONS

- Battery protection applications
- Load switch

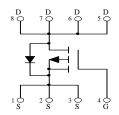
MARKING



Front side

Q4407= Device code
Solid dot=Pin1 indicator
Solid dot = Green molding compound device,
if none, the normal device
YY=Date Code

Equivalent Circuit



MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V _{GS}	±20	V
Continuous Drain Current	I _D	-12	А
Pulsed Drain Current	I _{DM}	-48	А
Single Pulsed Avalanche Energy	E _{AS} ⁽¹⁾	115	mJ
Power Dissipation	P _D	1.4	W
Thermal Resistance from Junction to Ambient	R _{0JA}	89	°C/W
Junction Temperature	TJ	150	°C
Storage Temperature Range	T _{stg}	-55 ~+150	°C
Lead Temperature for Soldering Purposes(1/8" from case for 10s)	TL	260	°C

^{(1).} E_{AS} condition: V_{DD} =-50V,L=0.5mH, R_{G} =25 Ω , Starting T_{J} = 25 $^{\circ}$ C

MOSFET ELECTRICAL CHARACTERISTICS

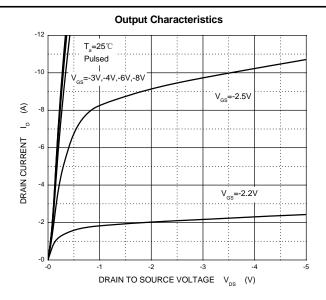
 T_a =25 $^{\circ}$ C unless otherwise specified

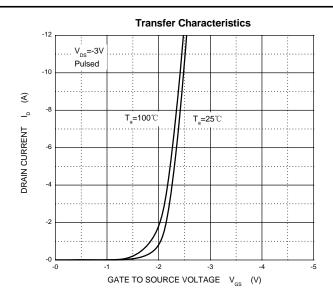
Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Off characteristics		•	•			
Drain-source breakdown voltage	V(BR) DSS	V _{GS} = 0V, I _D =-250µA	-30			V
Zero gate voltage drain current	I _{DSS}	V _{DS} =-30V, V _{GS} =0V			-1	μΑ
Gate-body leakage current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	nA
On characteristics (note1)			•			
Gate-threshold voltage	VGS(th)	V _{DS} =V _{GS} , I _D =-250μA	-1.0	-1.5	-2.2	V
Chatin durin accuracy on acts resistance	D	V _{GS} =-10V, I _D =-12A		7.8	13	mΩ
Static drain-source on-sate resistance	RDS(on)	V _{GS} =-6V, I _D =-10A		9	17	mΩ
Forward transconductance	$g_{\scriptscriptstyle{FS}}$	V _{DS} =-5V, I _D =-15A	25			S
Dynamic characteristics (note 2)			•			
Input capacitance	C _{iss}			2900		
Output capacitance	Coss	V _{DS} =-15V,V _{GS} =0V, f =1MHz		410		pF
Reverse transfer capacitance	C _{rss}	- 1 - 11011 12	280]	
Switching characteristics (note 2)			•			
Total gate charge	Qg			48		
Gate-source charge	Q_{gs}	V _{DS} =-15V, V _{GS} =-10V, I _D =-10A		12		nC
Gate-drain charge	Q_{gd}	- 1010/4		14		
Turn-on delay time	t _{d(on)}			15		
Turn-on rise time	tr	V _{DD} =-15V,		11		
Turn-off delay time	t _{d(off)}	V_{GS} =-10V, R_{G} =3 Ω , R_{L} =1.25 Ω		44		ns
Turn-off fall time	t f	1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1		21		
Gate Resistance	R _g	$f = 1MHz, V_{DS} = 0V,$ $V_{GS} = 0V,$			3.6	Ω
Drain-Source Diode Characteristics						
Drain-source diode forward voltage(note1)	V_{SD}	V _{GS} =0V, I _S =-2A			-1.2	V
Continuous drain-source diode forward current	Is				-15	А
Pulsed drain-source diode forward current	I _{SM}				-60	Α

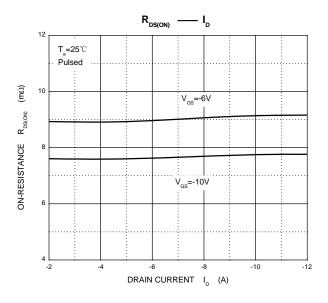
Notes:

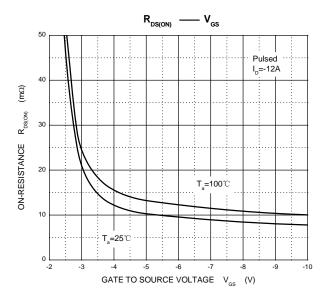
- 1. Pulse Test : Pulse Width≤300µs, duty cycle ≤2%.
- 2. Guaranteed by design, not subject to production testing.

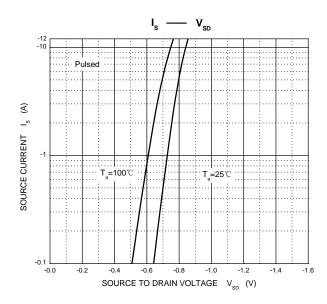
Typical Characteristics

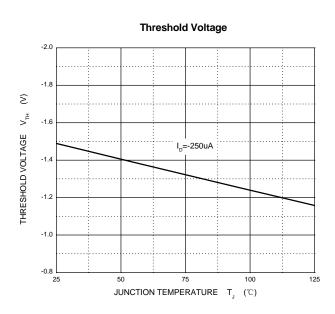




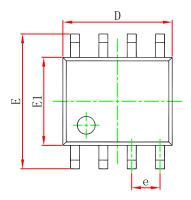


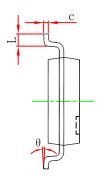


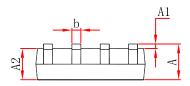




SOP8 Package Outline Dimensions

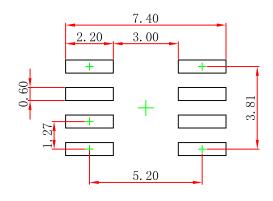






Symbol	Dimensions In	Millimeters	Dimensions In Inches		
Symbol	Min	Max	Min	Max	
A	1.350	1.750	0.053	0.069	
A1	0.100	0. 250	0.004	0.010	
A2	1.350	1.550	0.053	0.061	
b	0.330	0.510	0.013	0.020	
c	0.170	0.250	0.007	0.010	
D	4.800	5.000	0.189	0.197	
e	1. 270	(BSC)	0.050 (BSC)		
E	5.800	6.200	0. 228	0. 244	
E1	3.800	4.000	0.150	0.157	
L	0.400	1.270	0.016	0.050	
θ	0°	8°	0°	8°	

SOP8 Suggested Pad Layout



Note:

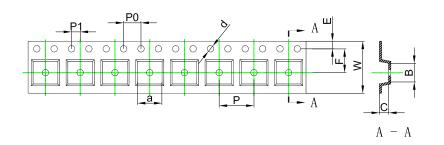
- 1. Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
- 3. The pad layout is for reference purposes only.

NOTICE

JCET reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to any product herein. JCET does not assume any liability arising out of the application or use of any product described herein.

SOP8 Tape and Reel

SOP8 Embossed Carrier Tape



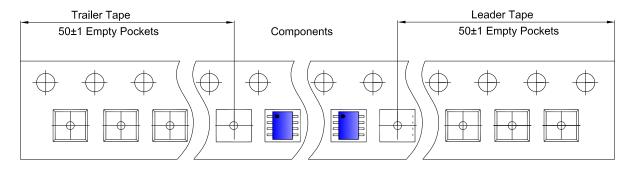
Packaging Description:

SOP8 parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 2,500 units per 13" or 33cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).

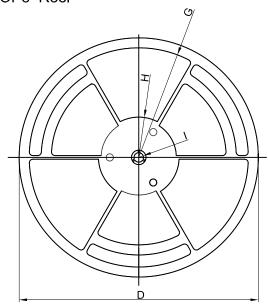
ALL DIM IN mm

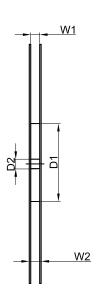
Dimensions are in millimeter										
Pkg type a B C d E F P0 P P1 W								W		
SOP8	6.40	5.40	2.10	Ø1.50	1.75	5.50	4.00	8.00	2.00	12.00

SOP8 Tape Leader and Trailer



SOP8 Reel





Dimensions are in millimeter								
Reel Option D D1 D2 G H I W1 W2								W2
13"Dia	Ø330.00	100.00	13.00	R151.00	R56.00	R6.50	12.40	17.60

REEL	Reel Size	Вох	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
4,000 pcs	13 inch	8,000 pcs	360×360×65	64,000 pcs	565×380×390	